

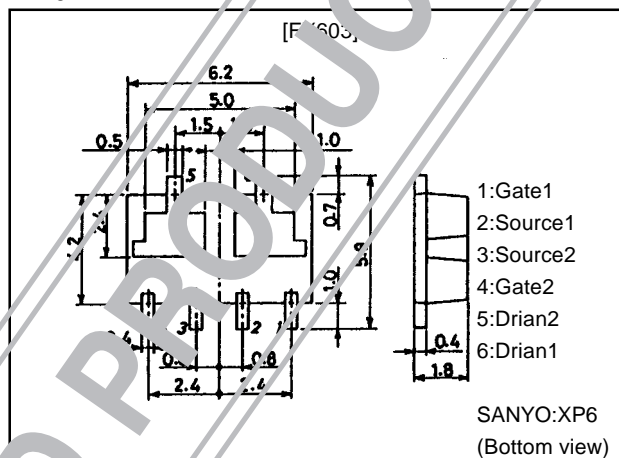
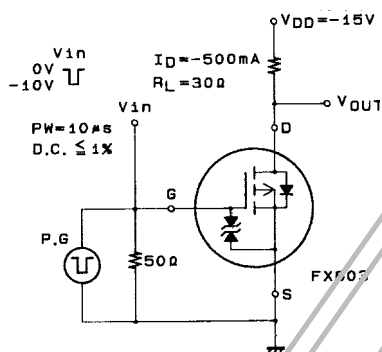
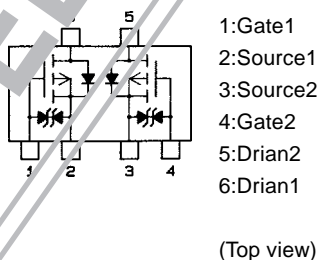
SANYO**FX603****P-Channel Silicon MOSFET****Ultrahigh-Speed Switching Applications****Features**

- Composite type composed of two low ON-resistance P-channel MOSFET chips for ultrahigh-speed switching and low-voltage drive.
- Facilitates high-density mounting.
- The FX603 is formed with two chips, each being equivalent to the 2SJ187, placed in one package.
- Matched pair characteristics.

Package Dimensions

unit:mm

2120

**Switching Time Test Clrcuit****Electrical Connection****Specifications**

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		-30	V
Gate-to-Source Voltage	V_{GS}		±15	V
Drain Current (DC)	I_D		-1	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	-4	A
Allowable Power Dissipation	P_D	Tc=25°C, 1unit	6	W
	P_D	Mounted on ceramic board (750mm ² ×0.8mm) 1unit	1.5	W
Total Dissipation	P_T	Mounted on ceramic board (750mm ² ×0.8mm)	2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

· Marking:603

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SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

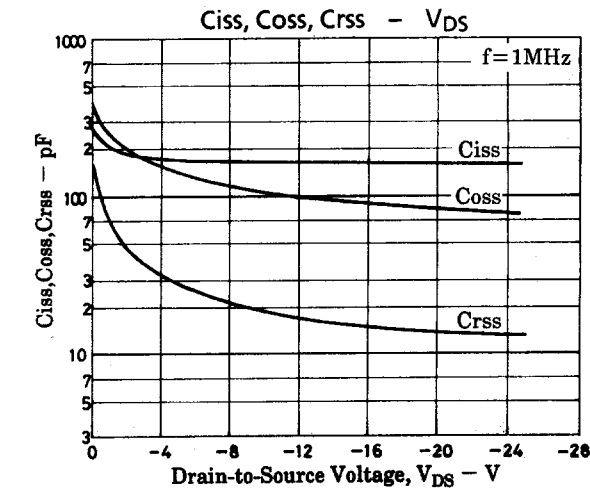
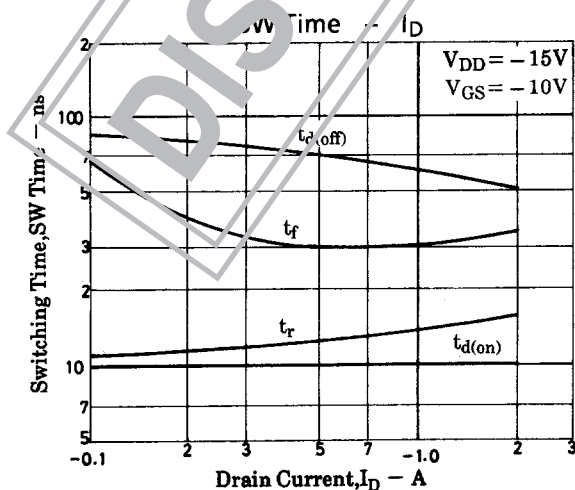
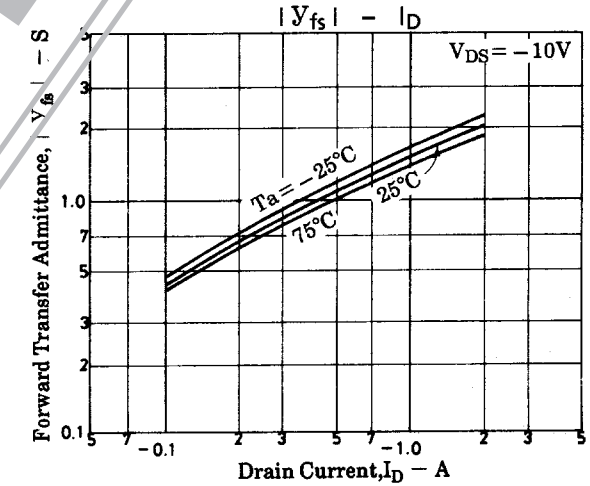
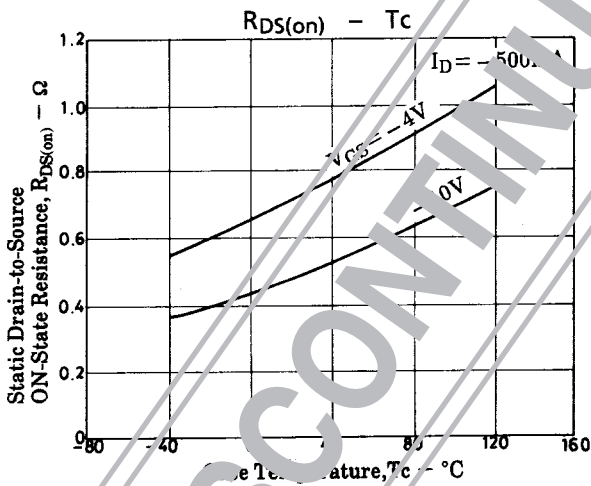
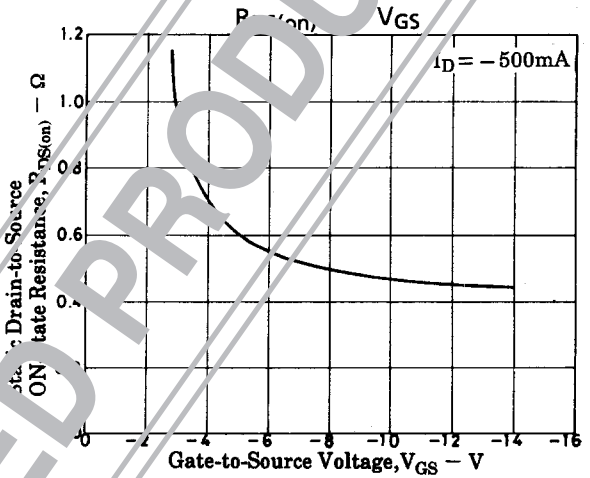
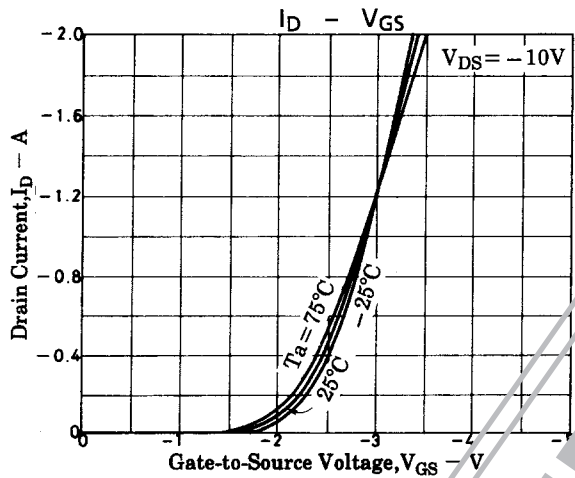
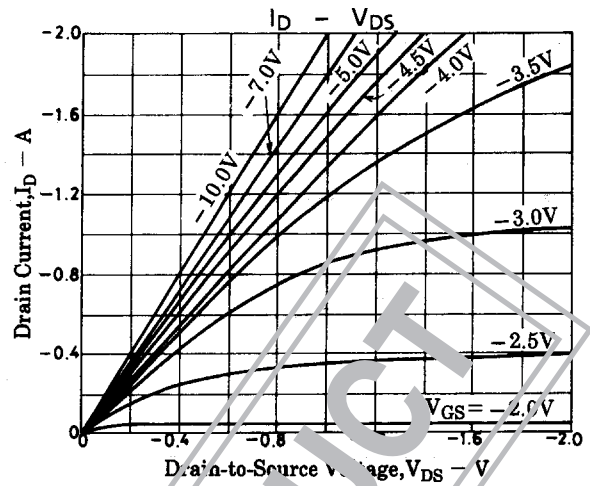
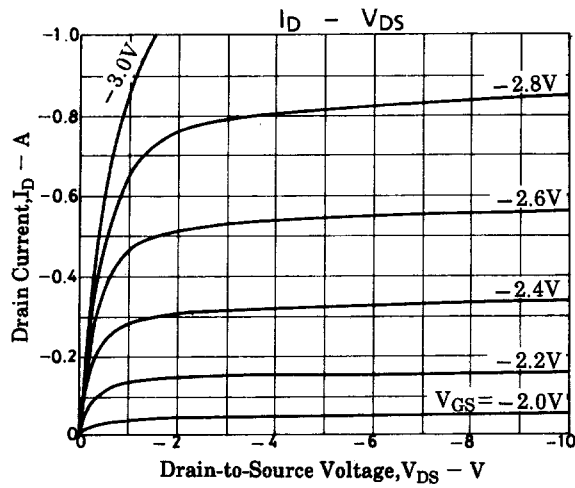
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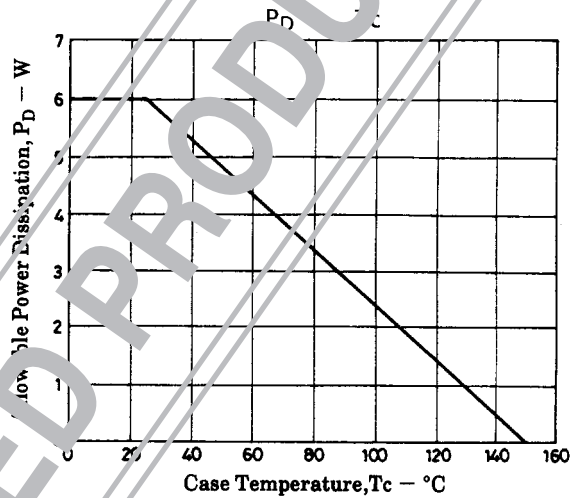
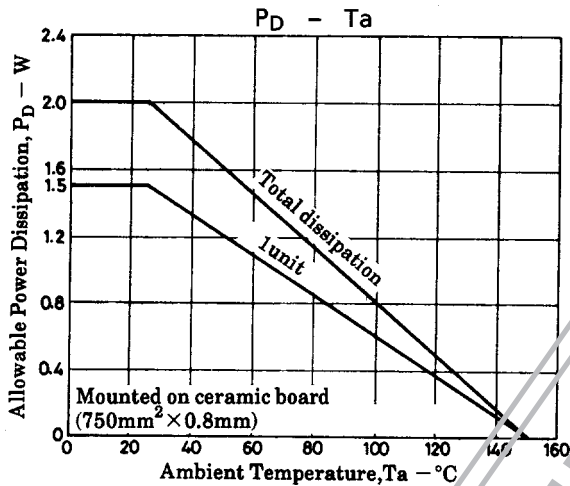
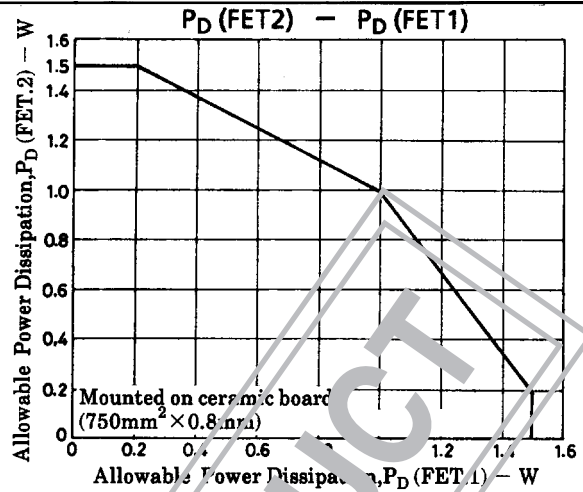
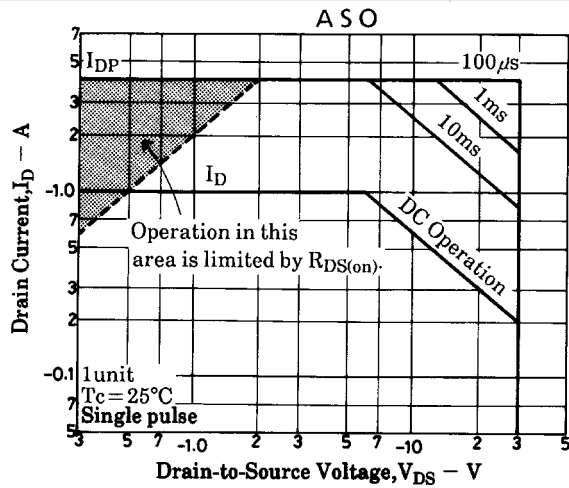
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Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}$, $V_{GS} = 0$	-50			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{V}$, $V_{GS} = 0$			-100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12$, $V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}$, $I_D = -1\text{mA}$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10\text{V}$, $I_D = -500\text{mA}$	0	1.0		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$I_D = -500\text{mA}$, $V_{GS} = -10\text{V}$		0.5	0.75	Ω
	$R_{DS(on)}$	$I_D = -500\text{mA}$, $V_{GS} = -4\text{V}$		0.5	1.1	Ω
Input Capacitance	C_{iss}	$V_{DS} = -10\text{V}$, $f = 1\text{MHz}$		170		pF
Output Capacitance	C_{oss}	$V_{DS} = -10\text{V}$, $f = 1\text{MHz}$		110		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -10\text{V}$, $f = 1\text{MHz}$		20		pF
Turn-ON Delay Time	$t_{d(on)}$	See Specified Test Circuit		10		ns
Rise Time	t_r	See Specified Test Circuit		13		ns
Turn-OFF Delay Time	$t_{d(off)}$	See Specified Test Circuit		70		ns
Fall Time	t_f	See Specified Test Circuit		30		ns
Diode Forward Voltage	V_{SD}	$I_S = -1\text{A}$, $V_{GS} = 0$		-0.9		V

DISCONTINUED PRODUCT





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